

Title (en)

DEVICE MANUFACTURE INVOLVING PATTERN DELINEATION IN THIN LAYERS.

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER ANORDNUNG UNTER VERWENDUNG VON STREIFENMUSTERN IN DÜNNSCHICHTEN.

Title (fr)

FABRICATION D'UN DISPOSITIF COMPORTANT UNE TRACE DE MODELES DANS DES COUCHES FINES.

Publication

EP 0035529 A1 19810916 (EN)

Application

EP 80901737 A 19810309

Priority

US 7140879 A 19790830

Abstract (en)

[origin: WO8100646A1] Etch procedures are monitored electrically by initiation of current flow upon baring of conducting surface (19) to etching fluid (11). Procedures include photoresist development in which current flow is through the usual aqueous ionic developing solution. In an exemplary use, a specifically designed monitoring wafer (10) serves for detection of end point for a batch of wafers undergoing processing.

Abstract (fr)

Des procedes de gravure sont controles electriquement par l'initiation d'un flux de courant sur la partie mise a nu d'une surface conductrice (19) exposee au fluide de gravure chimique (11). Les procedes comprennent ce developpement d'une photo reserve, dans lequel le flux de courant se produit a travers la solution aqueuse habituelle de developpement ionique. Dans une utilisation typique, une gaufrette de controle specifiquement concue (10) sert a detecter le point final pour un lot de gaufrettes en traitement.

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H01L 21/306

IPC 8 full level

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